

DATA SHEET

RX1214B80W; RX1214B130Y NPN microwave power transistors

Product specification
Supersedes data of November 1994

1997 Feb 14

NPN microwave power transistors

RX1214B80W; RX1214B130Y

FEATURES

- Suitable for short and medium pulse applications up to 1 ms pulse width, 10% duty factor
- Diffused emitter ballasting resistors improve ruggedness
- Interdigitated emitter-base structure provides high emitter efficiency
- Gold metallization with barrier realizes very stable characteristics and excellent lifetime
- Multicell geometry improves power sharing and reduces thermal resistance
- Internal input and output prematching networks allow an easier design of circuits.

APPLICATIONS

Common-base class C broadband pulsed power amplifiers for radar applications in the 1.2 to 1.4 GHz band. Also suitable for long pulse, heavy duty operation within this band.

DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a SOT439A metal ceramic flange package, with base connected to flange.

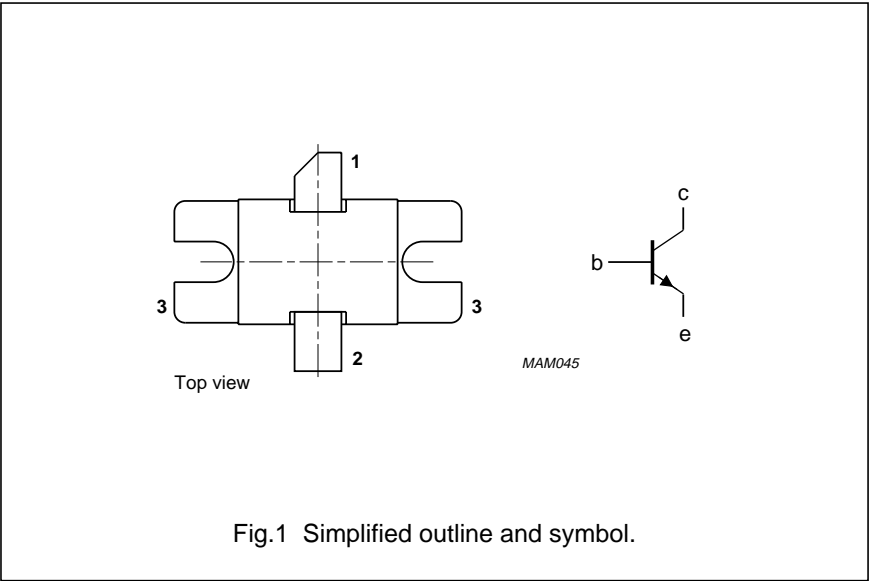
QUICK REFERENCE DATA

Microwave performance up to $T_{mb} = 25\text{ }^{\circ}\text{C}$ in a common-base class C narrowband amplifier.

MODE OF OPERATION	CONDITIONS	f (GHz)	V _{CC} (V)	P _L (W)	G _p (dB)	η _c (%)
Class C RX1214B80W	t _p = 500 μs; δ = 10%	1.2 to 1.4	40	≥80	≥7	≥35
Class C RX1214B130Y	t _p = 150 μs; δ = 5%	1.2 to 1.4	50	≥130	≥7	≥35

PINNING - SOT439A

PIN	DESCRIPTION
1	collector
2	emitter
3	base connected to flange



WARNING
Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO slab is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

NPN microwave power transistors

RX1214B80W; RX1214B130Y

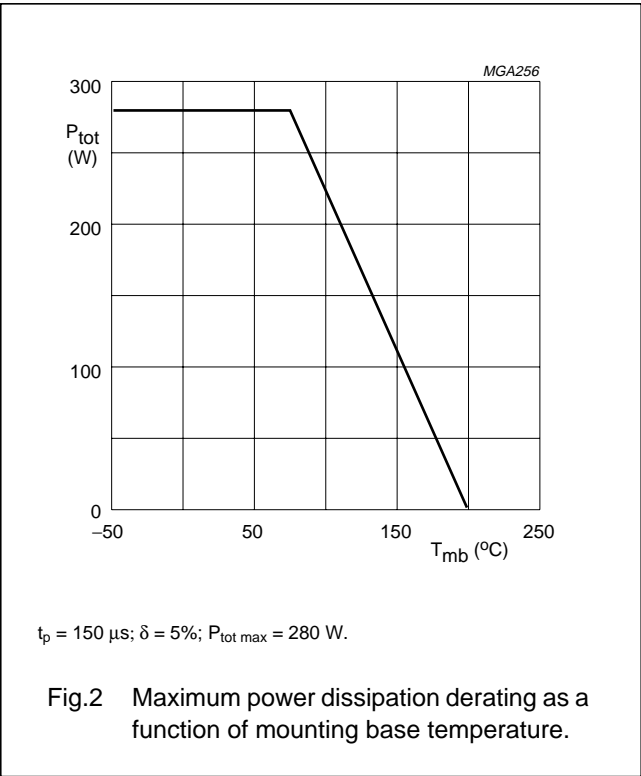
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	–	65	V
V _{CEO}	collector-emitter voltage	open base	–	15	V
V _{CES}	collector-emitter voltage	R _{BE} = 0 Ω	–	60	V
V _{EBO}	emitter-base voltage	open collector	–	3	V
I _C	collector current (DC)	t _p ≤ 150 μs; δ ≤ 5%	–	9	A
P _{tot}	total power dissipation	T _{mb} < 75 °C; t _p ≤ 150 μs; δ ≤ 5%	–	280	W
T _{stg}	storage temperature		–65	+200	°C
T _j	operating junction temperature		–	200	°C
T _{sld}	soldering temperature	t ≤ 10 s; note 1	–	235	°C

Note

1. Up to 0.2 mm from ceramic.



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RX1214B80W; RX1214B130Y

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	$T_j = 120\ ^\circ\text{C}$	1.75	K/W
$R_{th\ mb-h}$	thermal resistance from mounting base to heatsink	note 1	0.2	K/W
$Z_{th\ j-h}$	thermal impedance from junction to heatsink	$t_p = 150\ \mu\text{s}$; $\delta = 5\%$; notes 1 and 2	0.4	K/W

Notes

1. See "Mounting recommendations in the General part of handbook SC19a".
2. Equivalent thermal impedance under pulsed microwave operating conditions.

CHARACTERISTICS

$T_{mb} = 25\ ^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0$; $V_{CB} = 50\ \text{V}$	–	6	mA
I_{EBO}	emitter cut-off current	$I_C = 0$; $V_{EB} = 1.5\ \text{V}$	–	0.6	mA
$V_{(BR)CES}$	collector-emitter breakdown voltage	$I_C = 60\ \text{mA}$; $V_{BE} = 0$	60	–	V

APPLICATION INFORMATION

Microwave performance up to $T_{mb} = 25\ ^\circ\text{C}$ in a common-base test circuit as shown in Fig.3.

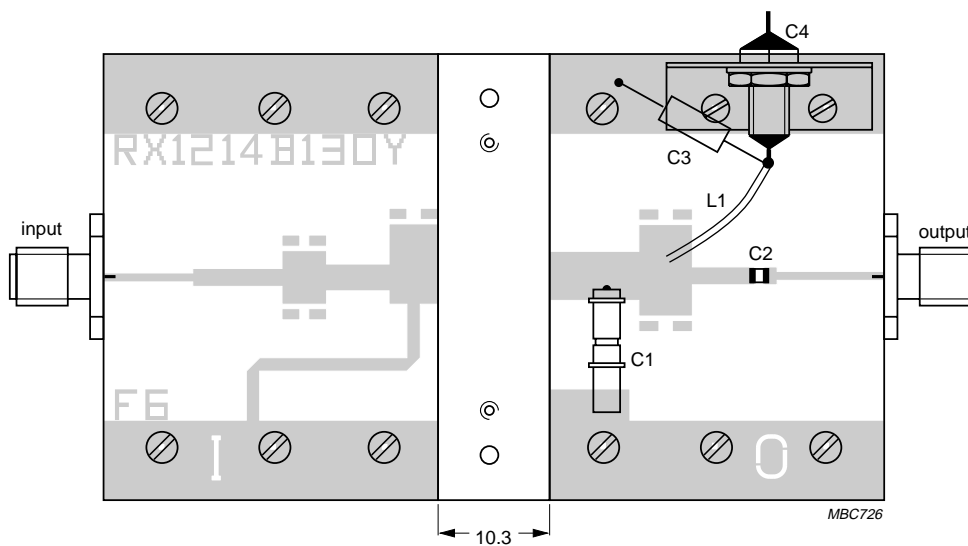
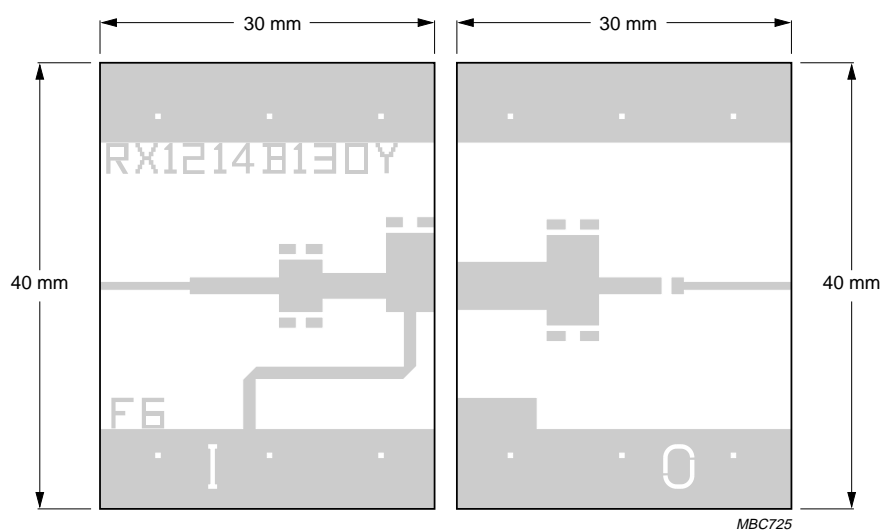
MODE OF OPERATION	CONDITIONS	f (GHz)	V_{CC} (V)	P_L (W)	G_p (dB)	η_c (%)
Class C	$t_p = 150\ \mu\text{s}$; $\delta = 5\%$	1.2 to 1.4	50	≥ 130 ; typ. 140	≥ 7 ; typ. 7.5	≥ 35 ; typ. 39
	$t_p = 500\ \mu\text{s}$; $\delta = 10\%$	1.2 to 1.4	40	typ. 80	typ. 8.5	typ. 40

List of components (see Fig.3)

COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE NO.
L1	0.5 mm copper wire		total length = 15 mm	
C1	trimmer capacitor	0.6 – 5 pF		Tekelec, ref AT3-7271SL
C2	chip capacitor			
C3	tantalum capacitor	10 μF , 50 V		
C4	feedthrough bypass capacitor			Erie, ref.1250-003

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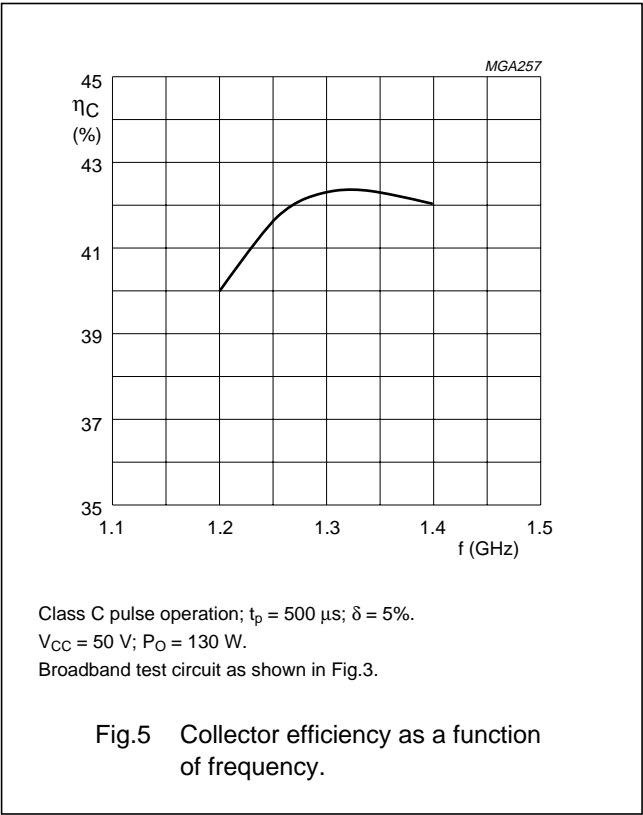
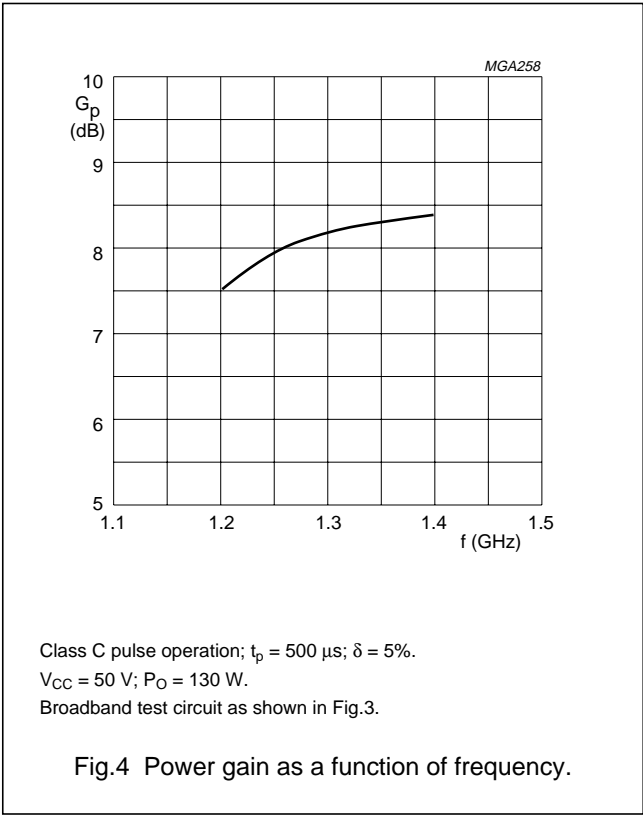


Substrate: Epsilam 10.
 Thickness: 0.635 mm.
 Permittivity: $\epsilon_r = 10$.

Fig.3 Broadband test circuit.

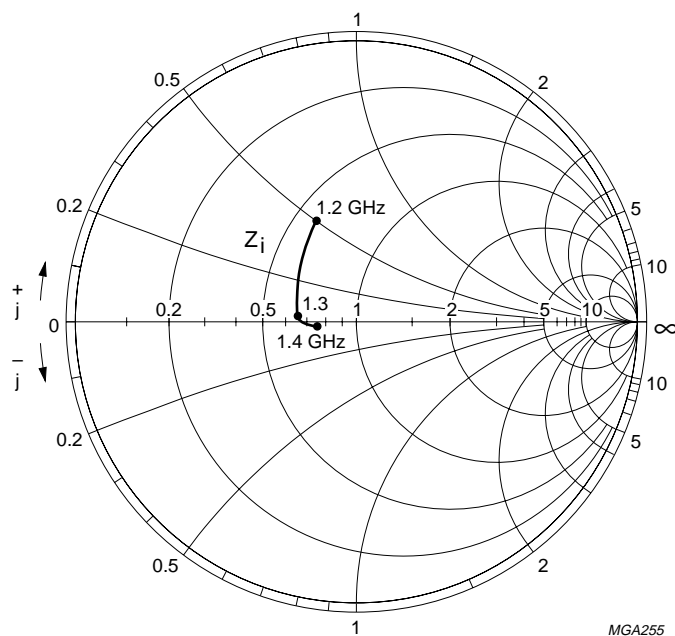
NPN microwave power transistors

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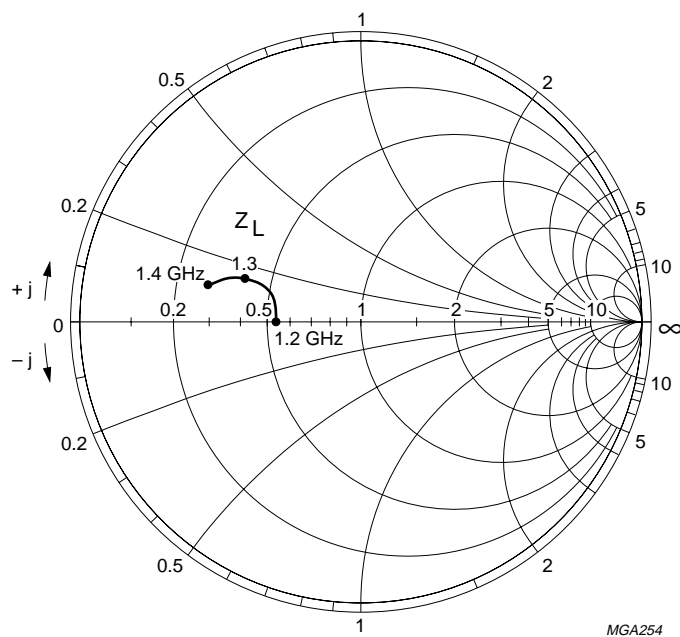
NPN microwave power transistors

RX1214B80W; RX1214B130Y



$V_{CC} = 50 \text{ V}$; $Z_O = 10 \Omega$; $P_{OUT} = 130 \text{ W}$.

Fig.6 Input impedance as a function of frequency, associated with optimum load impedance.



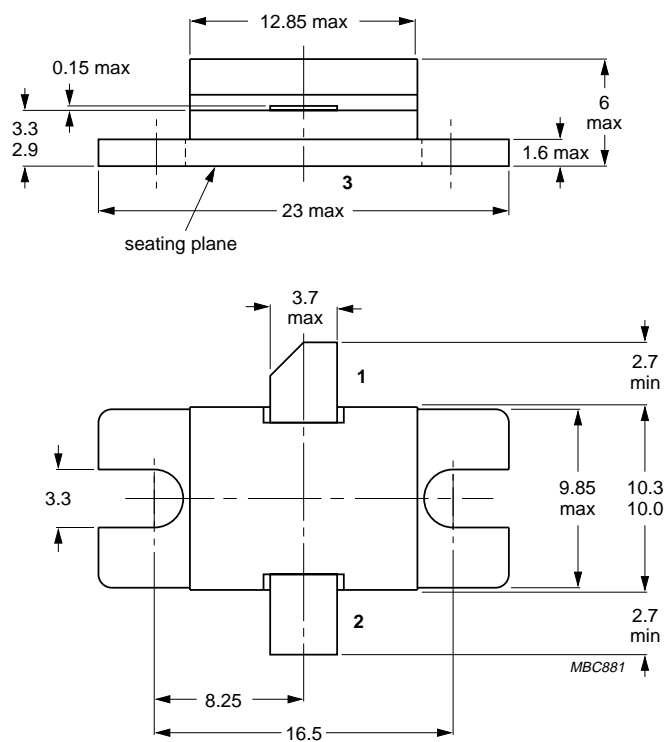
$V_{CC} = 50 \text{ V}$; $Z_O = 10 \Omega$; $P_{OUT} = 130 \text{ W}$.

Fig.7 Load impedance as a function of frequency, associated with optimum input impedance.

NPN microwave power transistors

RX1214B80W; RX1214B130Y

PACKAGE OUTLINE



Dimensions in mm.

Torque on nut: max 0.4 Nm.

Recommended screw: M3.

Recommended pitch for mounting screw: 19 mm.

Fig.8 SOT439A.

NPN microwave power transistorsRX1214B80W; RX1214B130Y

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

NPN microwave power transistors

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NOTES

NPN microwave power transistors

RX1214B80W; RX1214B130Y

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